

[MEMORY DEVICE AND FABRICATION METHOD THEREOF]

Abstract

The present invention relates to a memory device and the fabrication method thereof. A plurality of pairs of floating gates and a plurality of pairs of select gates are formed above each active region. After forming a dielectric layer on each floating gate and on each select gate, a plurality of pairs of word lines and a plurality of pairs of source lines are formed simultaneously. The word lines and the source lines are disposed in a direction vertical to the strip active regions. A plurality of source/drain regions is disposed in the substrate beside the word lines and the source lines. After forming a thick dielectric layer over the substrate, a plurality of source line contacts are formed in the thick dielectric layer for connecting the source/drain regions that are between each pair of source lines and at least connecting one of each pair of the source lines.